BCR20KM-12L

Triac

Medium Power Use

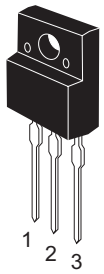
REJ03G0329-0200
Rev.2.00
Nov.09.2004

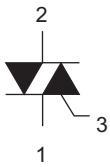
Features

- $I_{T\,(RMS)}$: 20 A
- V_{DRM} : 600 V
- I_{FGTI}, I_{RGTI}, I_{RGT} : 30 mA (20 mA)[Note5]
- Viso : 2000 V
- Insulated Type
- Planar Passivation Type
- UL Recognized : Yellow Card No. E223904
  File No. E80271

Outline

TO-220FN





1. T_1 Terminal
2. T_2 Terminal
3. Gate Terminal

Applications

Vacuum cleaner, electric heater, light dimmer, copying machine, and other general controlling devices

Maximum Ratings

Parameter	Symbol	Voltage class	Unit
		12	
Repetitive peak off-state voltage[Note1]	V_{DRM}	600	V
Non-repetitive peak off-state voltage[Note1]	V_{DSM}	720	V

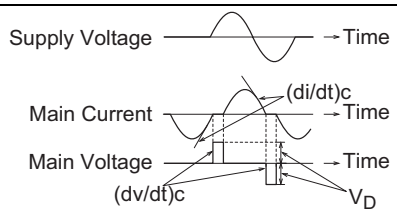
Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_{T\ (RMS)}$	20	A	Commercial frequency, sine full wave 360° conduction, Tc = 85°C
Surge on-state current	I_{TSM}	200	A	60Hz sinewave 1 full cycle, peak value, non-repetitive
I^2t for fusing	I^2t	167	A^2s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P_{GM}	5	W	
Average gate power dissipation	$P_{G\ (AV)}$	0.5	W	
Peak gate voltage	V_{GM}	10	V	
Peak gate current	I_{GM}	2	A	
Junction temperature	Tj	– 40 to +125	°C	
Storage temperature	Tstg	– 40 to +125	°C	
Mass	—	2.0	g	Typical value
Isolation voltage	Viso	2000	V	Ta = 25°C, AC 1 minute, $T_1 \cdot T_2 \cdot G$ terminal to case

Notes: 1. Gate open.

Electrical Characteristics

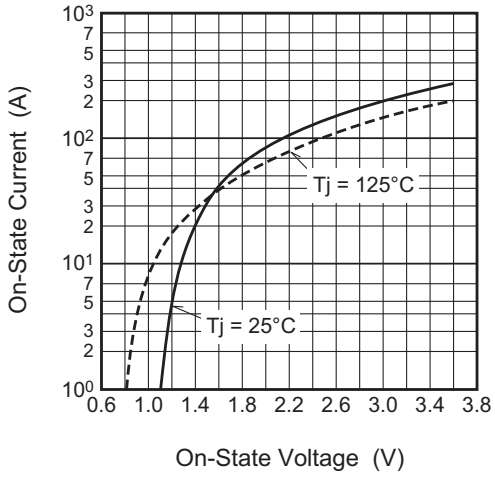
Parameter		Symbol	Min.	Typ.	Max.	Unit	Test conditions
Repetitive peak off-state current		I_{DRM}	—	—	2.0	mA	Tj = 125°C, V_{DRM} applied
On-state voltage		V_{TM}	—	—	1.5	V	Tc = 25°C, I_{TM} = 30 A, Instantaneous measurement
Gate trigger voltage[Note2]	I	V_{FGT_I}	—	—	1.5	V	Tj = 25°C, V_D = 6 V, R_L = 6 Ω, R_G = 330 Ω
	II	V_{RGT_I}	—	—	1.5	V	
	III	$V_{RGT_{III}}$	—	—	1.5	V	
Gate trigger current[Note2]	I	I_{FGT_I}	—	—	30[Note5]	mA	Tj = 25°C, V_D = 6 V, R_L = 6 Ω, R_G = 330 Ω
	II	I_{RGT_I}	—	—	30[Note5]	mA	
	III	$I_{RGT_{III}}$	—	—	30[Note5]	mA	
Gate non-trigger voltage		V_{GD}	0.2	—	—	V	Tj = 125°C, V_D = 1/2 V_{DRM}
Thermal resistance		$R_{th\ (j\text{-}c)}$	—	—	2.0	°C/W	Junction to case[Note3]
Critical-rate of rise of off-state commutating voltage[Note4]		(dv/dt)c	10	—	—	V/µs	Tj = 125°C

Notes: 2. Measurement using the gate trigger characteristics measurement circuit.
3. The contact thermal resistance $R_{th\ (c\text{-}f)}$ in case of greasing is 0.5°C/W.
4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.
5. High sensitivity ($I_{GT} \leq 20$ mA) is also available. (I_{GT} item: 1)

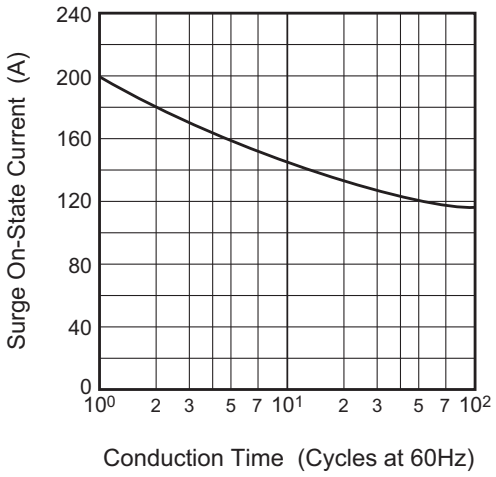
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature Tj = 125°C 2. Rate of decay of on-state commutating current (di/dt)c = –10 A/ms 3. Peak off-state voltage V_D = 400 V	

Performance Curves

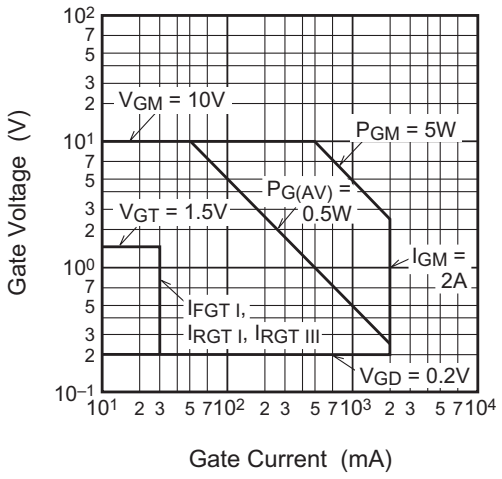
Maximum On-State Characteristics



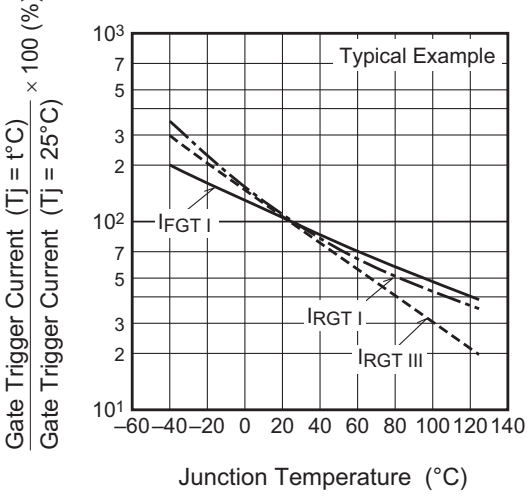
Rated Surge On-State Current



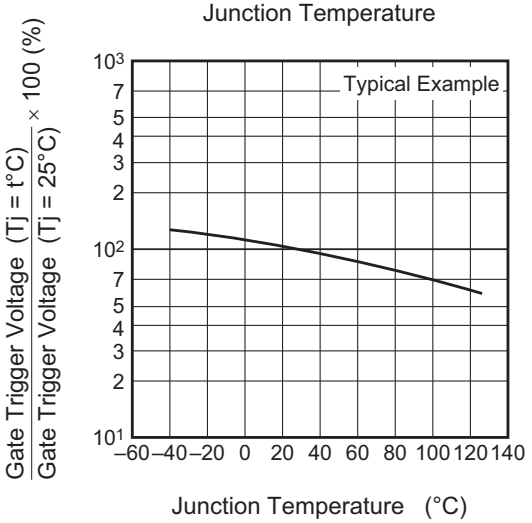
Gate Characteristics (I, II and III)



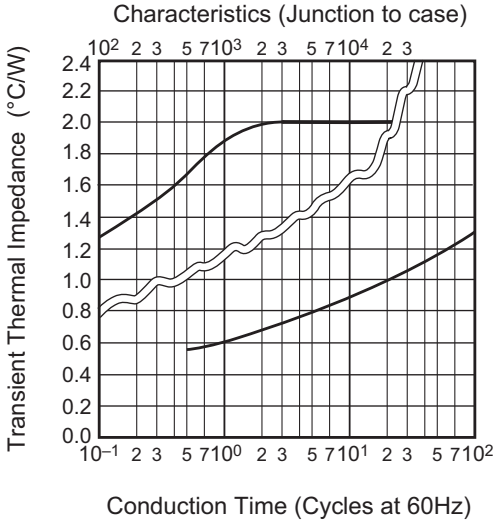
Gate Trigger Current vs. Junction Temperature



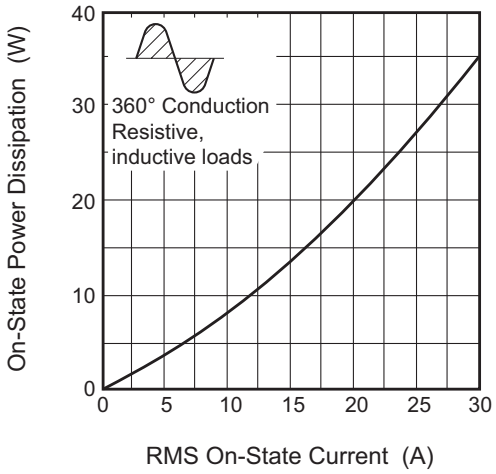
Gate Trigger Voltage vs. Junction Temperature



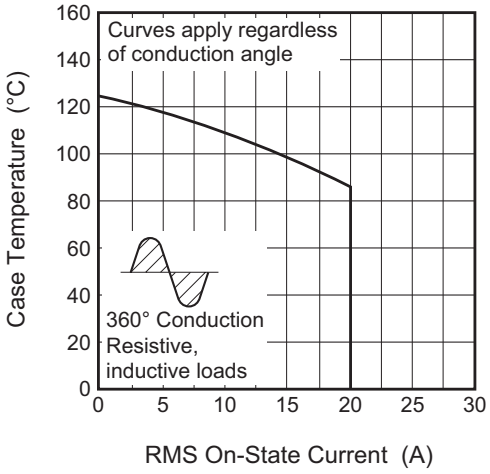
Maximum Transient Thermal Impedance Characteristics (Junction to case)



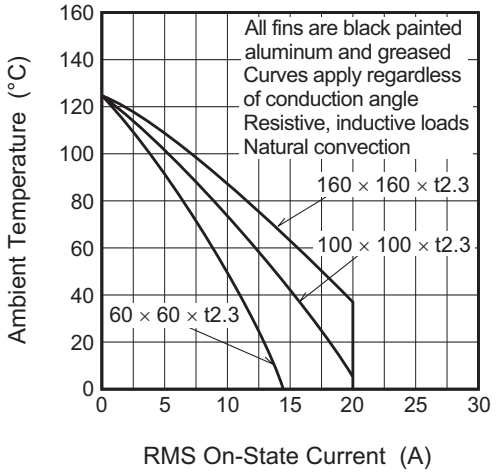
Maximum On-State Power Dissipation



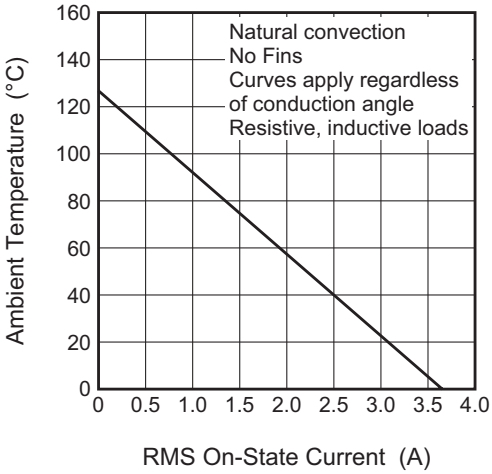
Allowable Case Temperature vs.
RMS On-State Current



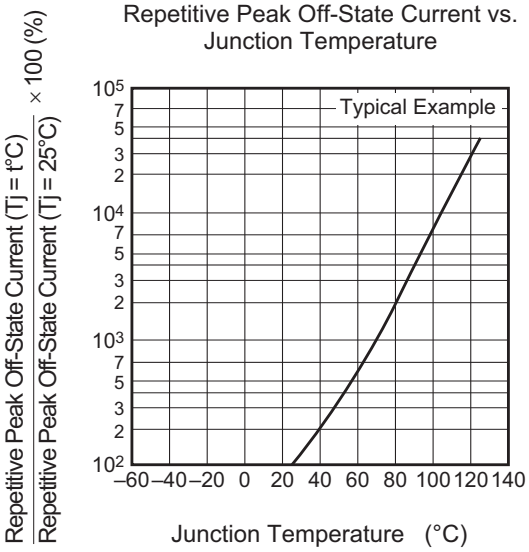
Allowable Ambient Temperature vs.
RMS On-State Current



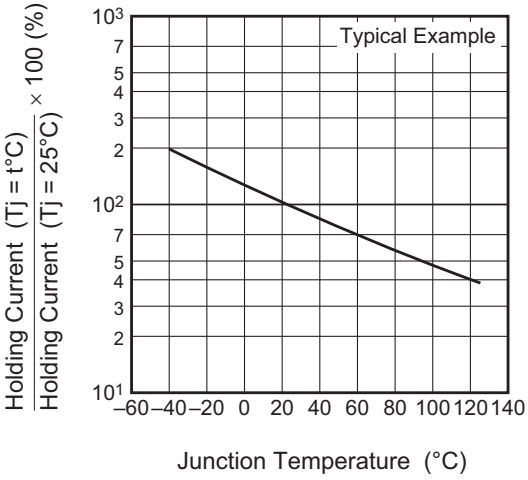
Allowable Ambient Temperature vs.
RMS On-State Current



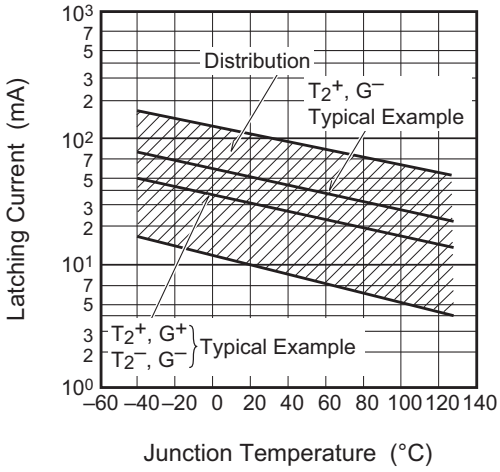
Repetitive Peak Off-State Current vs.
Junction Temperature



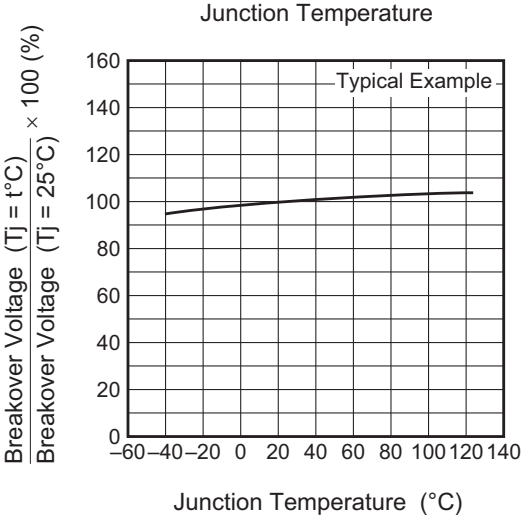
Holding Current vs.
Junction Temperature



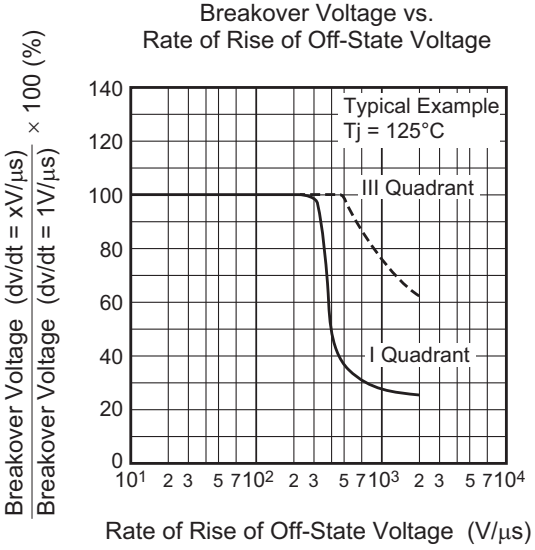
Latching Current vs.
Junction Temperature



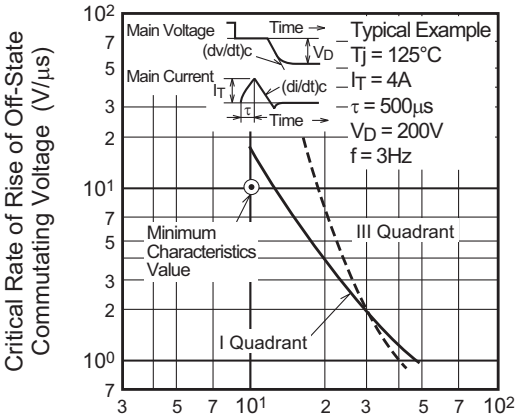
Breakover Voltage vs.
Junction Temperature



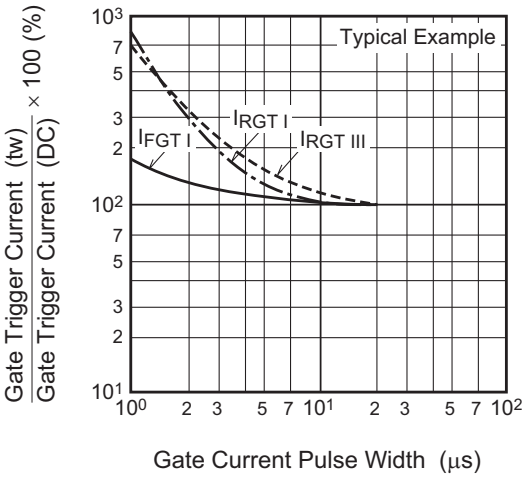
Breakover Voltage vs.
Rate of Rise of Off-State Voltage



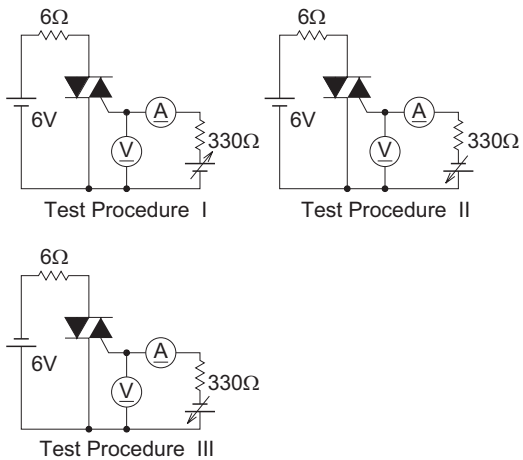
Commutation Characteristics



Gate Trigger Current vs.
Gate Current Pulse Width



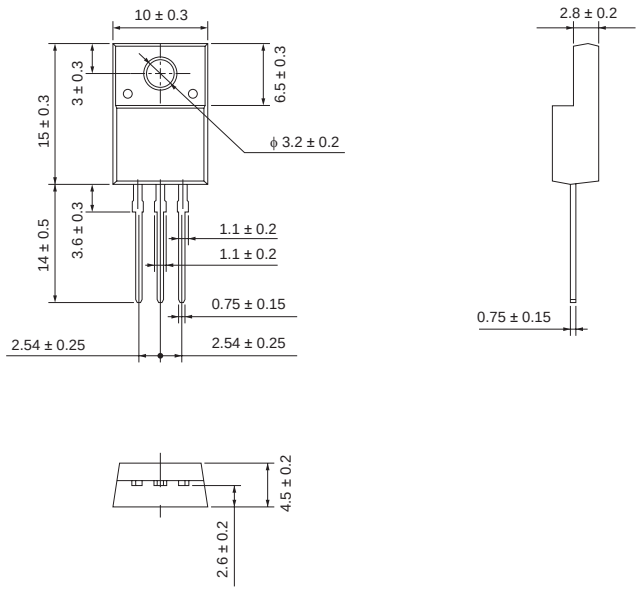
Gate Trigger Characteristics Test Circuits

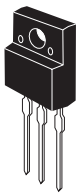


Package Dimensions

TO-220FN

EIAJ Package Code	JEDEC Code	Mass (g) (reference value)	Lead Material
—	—	2.0	Cu alloy





Note 1) The dimensional figures indicate representative values unless otherwise the tolerance is specified.

Symbol	Dimension in Millimeters		
	Min	Typ	Max
A			
A_1			
A_2			
b			
D			
E			
e			
x			
y			
y_1			
ZD			
ZE			

Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Plastic Magazine (Tube)	50	Type name +A	BCR20KM-12LA
Lead form	Plastic Magazine (Tube)	50	Type name +A – Lead forming code	BCR20KM-12LA-A8

Note : Please confirm the specification about the shipping in detail.

Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

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Renesas Technology America, Inc.
450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.
10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.
Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

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